

# ***EDI's x32 MCM-L SRAM Family: Integrated Memory Solution for TMS320C4x DSPs***

---

---

*APPLICATION REPORT: SPRA288*

*Tim Stahley  
Electronic Designs, Inc.*

*Digital Signal Processing Solutions  
March 1997*



## **IMPORTANT NOTICE**

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain application using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

**TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.**

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

## **TRADEMARKS**

TI is a trademark of Texas Instruments Incorporated.

Other brands and names are the property of their respective owners.

## CONTACT INFORMATION

US TMS320 HOTLINE	(281) 274-2320
US TMS320 FAX	(281) 274-2324
US TMS320 BBS	(281) 274-2323
US TMS320 email	dsph@ti.com

## Contents

<b>Abstract</b> .....	<b>7</b>
<b>Product Support</b> .....	<b>8</b>
World Wide Web .....	8
<b>Introduction</b> .....	<b>9</b>
<b>x32 MCM-L Family Architecture</b> .....	<b>10</b>
8L3265C and 8L32256C (64K/256Kx32 SRAM) Architecture .....	11
8L32128C and 8L32512C (128K/512Kx32) Architecture .....	12
<b>Block Diagrams</b> .....	<b>13</b>
x32 MCM-L Family Features and Benefits .....	16
<b>Interfacing to the TI TMS320C4x DSP</b> .....	<b>17</b>
Basic Interface to Local or Global Bus .....	18
Dual Strobe Interface (Two Memory Banks) .....	21
<b>Matching Memory Access to DSP Bus Frequency</b> .....	<b>23</b>
<b>Summary</b> .....	<b>24</b>

## Figures

Figure 1.	EDI8L3265C and EDI8L32256C Block Diagram .....	14
Figure 2.	EDI8L32128C and EDI8L32512C Block Diagram .....	15
Figure 3.	Basic Interface of TMS320C4x to the EDI8L3265C or EDI8L32256C .....	19
Figure 4.	Basic Interface of TMS320C4x to the EDI8L32128C or EDI8L32512C .....	20
Figure 5.	Dual Strobe Interface Between TMS320C4x and Two EDI8L32128C .....	22

## Tables

Figure 1.	EDI8L3265C and EDI8L32256C Block Diagram .....	14
Figure 2.	EDI8L32128C and EDI8L32512C Block Diagram .....	15
Figure 3.	Basic Interface of TMS320C4x to the EDI8L3265C or EDI8L32256C .....	19
Figure 4.	Basic Interface of TMS320C4x to the EDI8L32128C or EDI8L32512C .....	20
Figure 5.	Dual Strobe Interface Between TMS320C4x and Two EDI8L32128C .....	22

# EDI's x32 MCM-L SRAM Family: Integrated Memory Solution for TMS320C4x DSPs

---

---

---

## Abstract

Memory modules have long been a system designer's trump card. Modules, in addition to the traditional space savings, allow ease of implementation, known operating performance, flexible density options and the ability to move across technology boundaries (i.e. CMOS to BiCMOS) without changing their system board design. As technology innovations continue, both at the chip and assembly levels, modules are no longer saddled by performance penalties associated with system board interfaces. Today's modules achieve equivalent or in some cases improved performance over traditional monolithic approaches. This performance improvement is linked to reductions in capacitance and inductance as well as improved power planes and signal line impedance versus a monolithic solution. This application report will show how these benefits can be taken advantage of in a system design using Texas Instrument's TMS320C4x DSPs.



## Product Support

### World Wide Web

Our World Wide Web site at [www.ti.com](http://www.ti.com) contains the most up to date product information, revisions, and additions. Users registering with TI&ME can build custom information pages and receive new product updates automatically via email.

TMS320C4x datasheets available on-line at [www.ti.com](http://www.ti.com). EDI datasheets are available on-line at: [www.electronic-designs.com](http://www.electronic-designs.com)





## Introduction

How often during a design cycle do your system requirements change? Have you ever been at the end of your design cycle and had the memory requirements increased two to four times the density the initial design required? As competition and cost pressures increase, the need for multi-function and multi-application designs has become a requirement as opposed to a benefit. In many cases, changing the density, access time or technology of the memory array provides the required flexibility for multi-application designs. For example, a DSP board design with a high density BiCMOS memory array will meet the high-end performance market while changing the memory to lower density CMOS or Flash array will allow the design to meet the requirements of the cost sensitive consumer market. Designing in this type of flexibility can lead to complex board designs and excessive board costs. What if all these options came in a single package with a compatible footprint? How many problems would it solve?

EDI has developed a family of x32 SRAM and Flash products that are packaged in a JEDEC standard 68 pin PLCC. The SRAM products are available in densities from 64Kx32 through 512Kx32 in both BiCMOS and CMOS technologies. The Flash products are available in densities from 128Kx32 through 512Kx32.

This application report will describe the SRAM products, detail proper interfacing to the TI TMS320C4x family of DSPs and provide the technical information required to take full advantage of these benefits. The 5V only Flash products, though not described in this report, are pin for pin compatible and provide additional options for cost sensitive applications.

## x32 MCM-L Family Architecture

EDI's x32 MCM-L family is a series of high performance SRAM arrays packaged in a JEDEC standard 68 pin PLCC. The x32 MCM-L family of devices currently range in density from 64Kx32 to 512Kx32.

The basic components of the architecture include : a single address bus , a single databus, a single write enable pin, a single output enable pin and four enable pins. The enable pins control individual bytes (8 bits) of the 32 bit databus.

The differences within the family lie in the address bus, which requires additional address lines for increased density and the addition of two enable pins for the 64Kx32 and the 256Kx32 densities. As the following block diagrams will show the 64Kx32 and the 256Kx32 are based on x16 SRAMs which provide two byte enable pins as well as a chip enable pin. The additional chip enable pin is required to place the device in low power, standby mode. The address bus and the enable configuration needs to be considered when designing a system which can take advantage of the multiple density options provided by the x32 MCM-L family.



## 8L3265C and 8L32256C (64K/256Kx32 SRAM) Architecture

The EDI8L3265C (64Kx32) and 8L32256C (256Kx32) are comprised of two x16 CMOS SRAMs, 64Kx16 and 256Kx16, respectively. The address buses, write enables and output enables of the two x16 SRAMs are internally connected between the two SRAM die providing a single address bus, write enable and output enable pin to the package pins. This provides a 50% reduction in signal connections required at the system board

Since the 8L3265C and the 8L32256C are designed using x16 SRAMs the enable configuration contains a chip enable (E\ ) and two byte selects (BS0 and BS1) per SRAM die. For the x32 array this leads to two chip enables (E0\ and E1\ ) as well as four byte selects (BS0-BS3). The byte selects provide the ability to perform byte (8 bit) wide operations while the chip enable pins allow word (16 bit) operations and are **required** to place the device in low power standby mode. Table 1 below, provides a truth table description on the Enable configuration.

*Table 1. Truth Table for EDI8L3265C and EDI8L32256C Enable Configuration*

Enable Pins						Databus	Function	Power
E1\	E0\	BS3\	BS2\	BS1\	BS0\	Status		
H	H	X	X	X	X	High Z	standby	standby
L	L	L	L	L	L	Data Out (W\ = H)	x32 Read	active
						Data In (W\ = L)	X32 Write	active
L	L	H	H	H	H	High Z	output disable	active
H	L	X	X	L	L	DQ31-DQ16 High Z	word operation (dependent on W\ status)	X16 active
						DQ15-DQ0 Active	(See Note)	
H	L	X	X	H	L	DQ31-DQ8 High Z	byte operation (dependent on W\ status)	X8 active
						DQ7-DQ0 Active	(See Note)	

Note: This is only an example. Operations on other bytes/words are achieved by enabling the desired byte/word. Please refer to datasheet or block diagram for reference.

## 8L32128C and 8L32512C (128K/512Kx32) Architecture

The EDI8L32128C (128Kx32) and EDI8L32512C (512Kx32) are comprised of four x8 CMOS SRAMs, 128Kx8 and 512Kx8, respectively. The address buses, write enables and output enables of the four x8 SRAMs are internally connected between the four SRAM die providing a single address bus, write enable and output enable pin to the package pins. This provides a 50% reduction in signal connections required at the system board

Since the 8L32128C and 8L32512C are designed using x8 SRAMs the enable configuration contains a chip enable (E\ per SRAM die. For the x32 array this leads to four chip enables (E0\ - E3\). In this case the chip enables provide the ability to perform byte (8 bit) wide operations as well as place the device in low power standby mode. Chip Enables (E0\ - E3\ occupy the same pins as the byte selects (BS0 - BS3) on the EDI8L3265C and EDI8L32256C, which are based on x16 SRAM devices. below provides a truth table description on the Enable configuration.

*Table 2. Truth Table for EDI8L32128C and EDI8L32512C Enable Configuration*

Enable Pins				Databus	Function	Power
E3\ X	E2\ X	E1\ X	E0\ X	Status High Z	standby	standby
L	L	L	L	Data Out (W\ = H) Data In *W\ = L)	x32 Read x32 Write	active active
H	H	L	L	DQ31-Dq16 High Z DQ15-DQ0 Active	word operation (dependent on W\ status) (See Note)	x16 active
H	H	H	L	DQ31-DQ8 High Z DQ7-DQ0 Active	byte operation (dependent on W\ status) (See Note)	x8 active

Note: This is only an example. Operations on other bytes/words are achieved by enabling the desired byte/word. Please refer to datasheet or block diagram for reference.



## Block Diagrams

Figure 1 shows a block diagram of the EDI8L3265C and EDI8L32256C. Figure 2 show a block diagram of the EDI8L32128C and EDI8L32512C. Shaded area in each diagram indicates the boundary of the PLCC package. All signal connections within the shaded area indicate connections internal to the PLCC package.

Figure 1. EDI8L3265C and EDI8L32256C Block Diagram

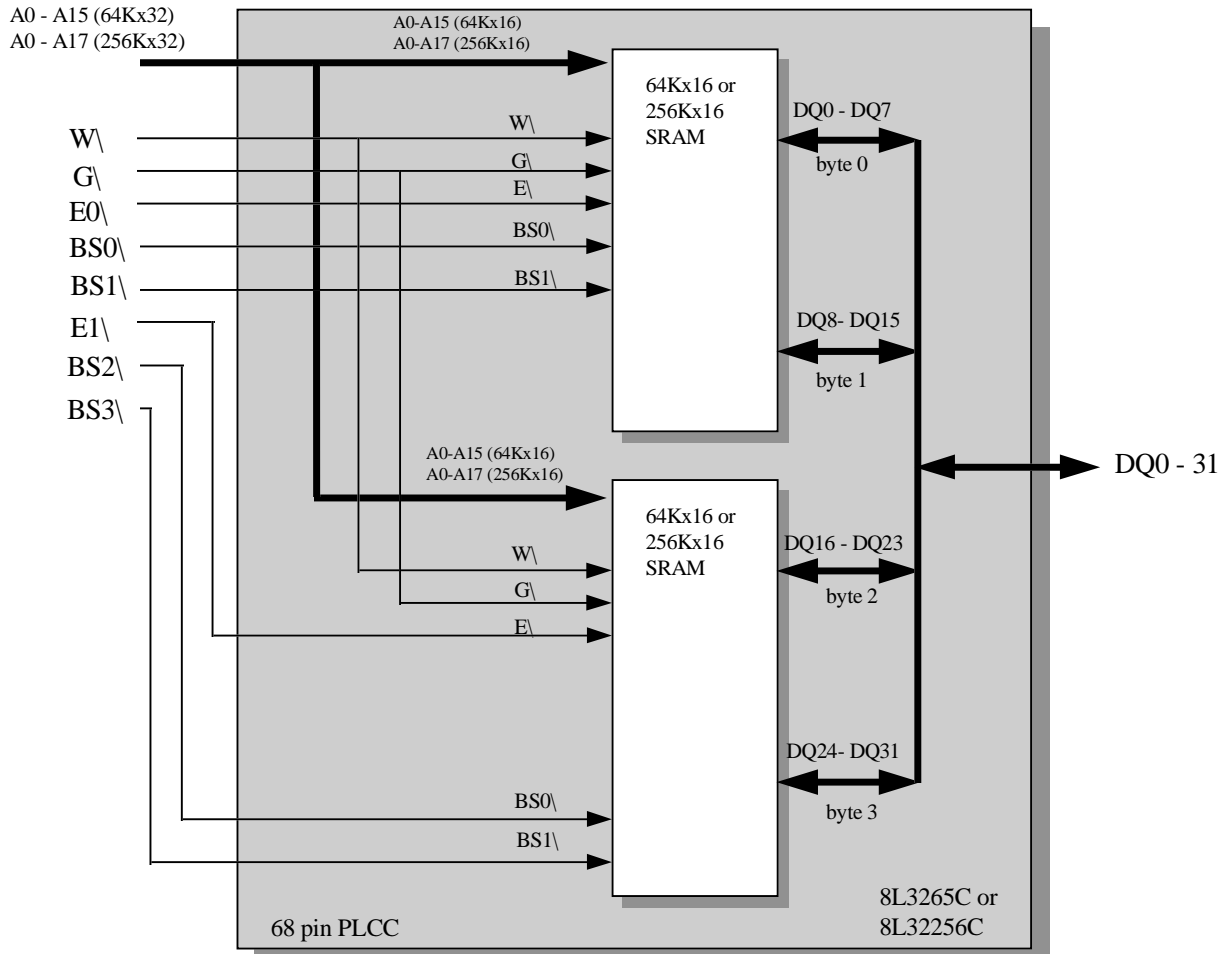
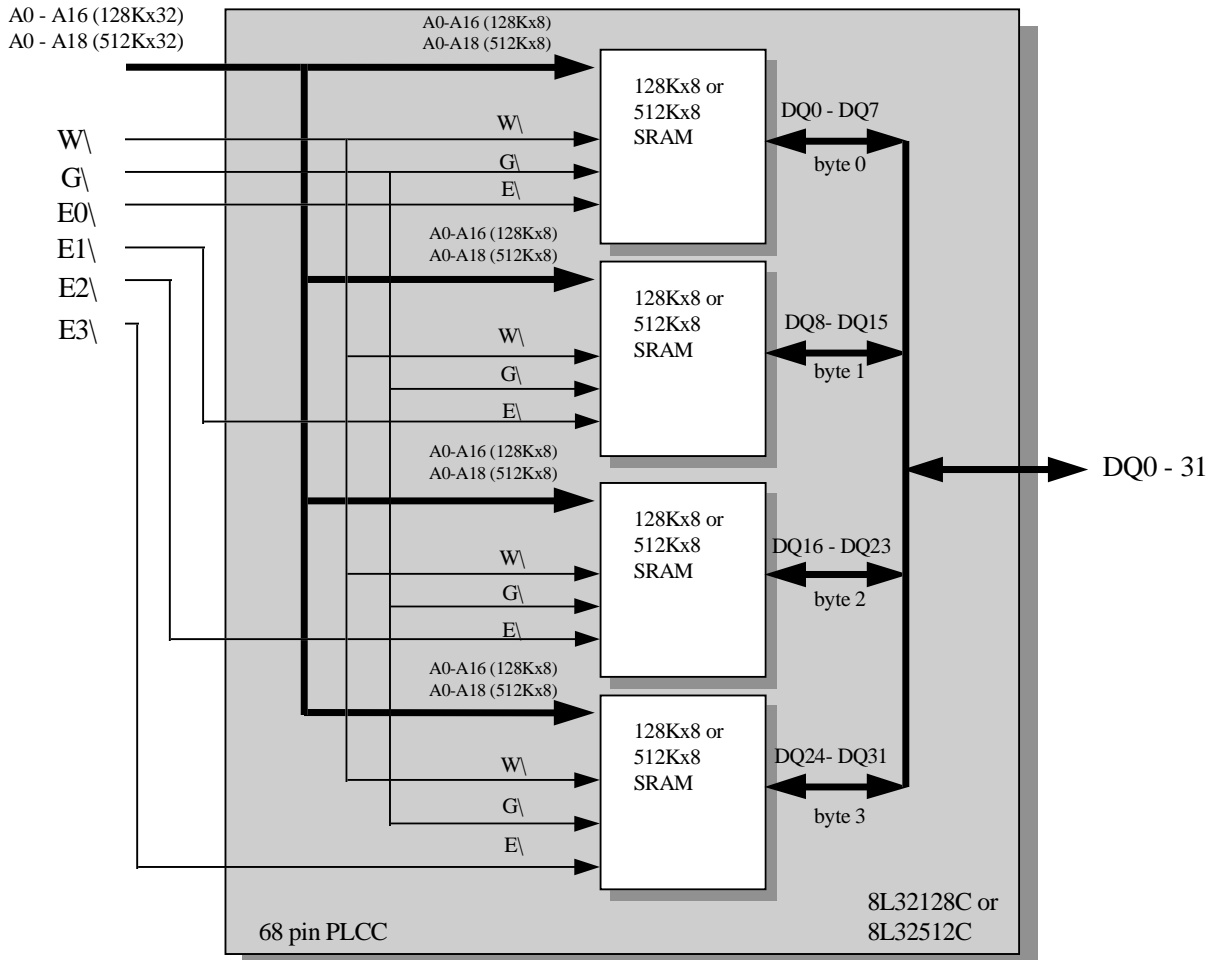




Figure 2. EDI8L32128C and EDI8L32512C Block Diagram



## x32 MCM-L Family Features and Benefits

Table 3 shows the features and benefits of the x32 MCM-L family, and compares the benefits of EDI8L32128C to the benefits of other common approaches for 128Kx32 memory array.

*Table 3. x32 MCM-L Family Features and Benefits*

Feature	Benefit
Single component x32 SRAM Array	Improved system performance, inventory reduction
Fast access times : BI-CMOS 8nS to 12nS CMOS 15nS to 45nS	Wide availability of speed ranges to fit each application. CMOS and BI-CMOS in same footprint
Individual byte enables	User configurable array size, x32, x16, or x8
Master write control and output enable	Provides glueless interface
Small footprint	System board space savings
68 lead PLCC (JEDEC MO-47AE)	Manufacturing: - pick and place operations - socket availability
Multiple VCC and VSS pins	Improved noise immunity (ground bounce)
Reduced inductance and capacitance	Improved signal integrity and noise immunity
Fully asynchronous	No clock circuitry required
Upgrade path available	Upgrade to 64Kx32 through 512Kx32 without redesigning system board

*Table 4. Comparison of Benefits*

Memory Solution	Component package	Components required	Number of connections at system board	Board space required	Upgrade Path
EDI8L32128C	68 pin PLCC	1	63	0.990 sq. in.	yes (through 512Kx32)
128Kx8 Monolithic	32pin 300mil PSOJ	4	120	1.689 sq. in.	no (512Kx8 in 36 pin)
128Kx8 Monolithic	32pin 400mil PSOJ	4	120	2.020 sq. in.	no (512Kx8 in 36 pin)





## Interfacing to the TI TMS320C4x DSP

The Texas Instruments TMS320C4x DSPs are 32 bit floating point digital signal processors, designed specifically for parallel processing and other real-time embedded applications. The C4X DSPs are used in a wide variety of applications including : image processing, 3-D graphics, speech recognition and high speed communications. The C4X family consists of the TMS320C40 and the TMS320C44.

The TMS320C4x DSPs external memory interface consists of two independent buses, the local bus and the global bus. The local bus typically interfaces to an exclusive memory array while the global bus typically interfaces to a shared (multi-processor) memory array. The local and global bus memory interfaces are identical and all examples in this report will refer to the global bus but be applicable to both the global and local bus. Memory interface components for the two buses differ in name only and are summarized in Table 5 below.

*Table 5. C4X Memory Interface Components (See Note)*

<b>Interface Component</b>	<b>Local bus signal name</b>	<b>Global Bus Signal Name</b>
32 bit data bus	LD0 - LD31	D0 - D31
31 bit address bus	LA0 - LA30	A0 - A30
Strobe pins	LSTRB0\ and LSTRB1\	STRB0\ and STRB1\
Read/Write signals	LR/W\0 and LR/W\1	R/W\0 and R/W\1
Ready signal	LRDY0\ and LRDY1\	RDY0\ and RDY1\

Note: Table 5 is a subset of Memory Interface components. It does not include signals required for multiprocessor interfacing. For a complete overview of the interface, refer to the TMS320C4x datasheets.

Basic Interface to Local or Global Bus discusses the basic interface between the C4X DSPs and EDI's x32 MCM-L SRAM products. In this case the strobe pin of the C4X is connected to the four chip enable pins, E0\ - E3\, of the memory array. The device enters low power standby mode whenever STRB0\ of the C4X is active high. E0\ - E3\ of the 128Kx32 and 512Kx32 are located on the same device pins as the BS0\ - BS3\ pins on the 64Kx32 and 256Kx32. Therefore when considering upgrade paths the decisions required are the connection of E0\ and E1\ on the 64Kx32 and the 256Kx32 and supplying the extra address signals required for the additional density.

Databus pins D31 - D0 of the TMS320C4x are connected to the corresponding DQ31 - DQ0 of the 8L32128C/512C.

Dual Strobe Interface (Two Memory Banks) discusses dual strobe interfacing, which enables two memory banks per memory interface (Local or Global).

## Basic Interface to Local or Global Bus

Interfacing to the EDI x32 MCM-L family to the TMS320C4x is straightforward. The databus of the EDI x32 MCM-L, DQ0 - DQ31 is connected directly to the databus, D0-D31, of the C4X. The connections may be one to one (D0 to DQ0, D1 to DQ1, etc.) or mixed in any combination (D0 to DQ12, D1 to DQ23, etc.). Since all operations are 32 bit the order is irrelevant.

### NOTE:

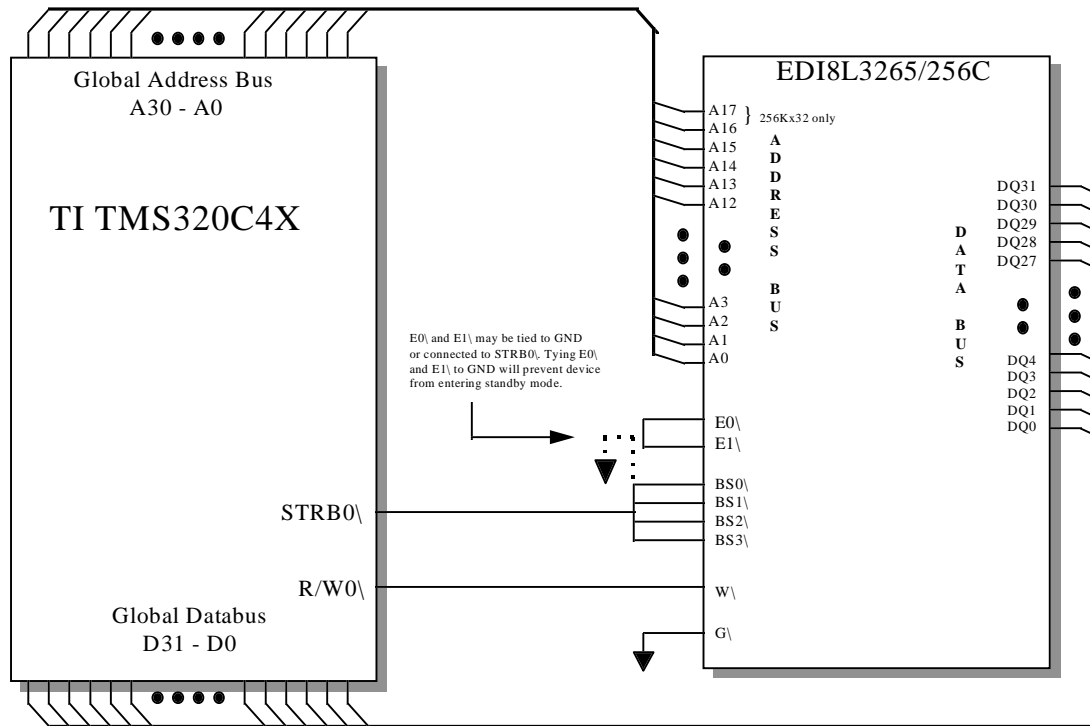
If design may also incorporate EDI's 68 pin Flash products in same socket, databuses must be connected one to one due to commands required for Flash product).

The memory control requires only two pins, the external strobe pin (STRB0) and the read/write pin (R/W0). The strobe pin acts as an enable pin and is connected to the chip enable pins of the x32 MCM-L product. As described earlier in the device architecture section, the Enable configuration differs slightly between the 64K/256Kx32 and the 128K/512Kx32 products. This difference needs to be accounted and is described in the following text. The read/write pin connects directly to the write enable pin on the x32 MCM-L products and controls write and read functionality.

The outputs are switched to a high impedance state via STRB0\ going high, (memory disable), or via R/W0\ pin going low (memory enters write mode). Therefore the output enable functionality is not required via the output enable (G\ pin and it may be tied to ground.

Figure 3 shows the basic interface to the EDI8L3265C/256C device.

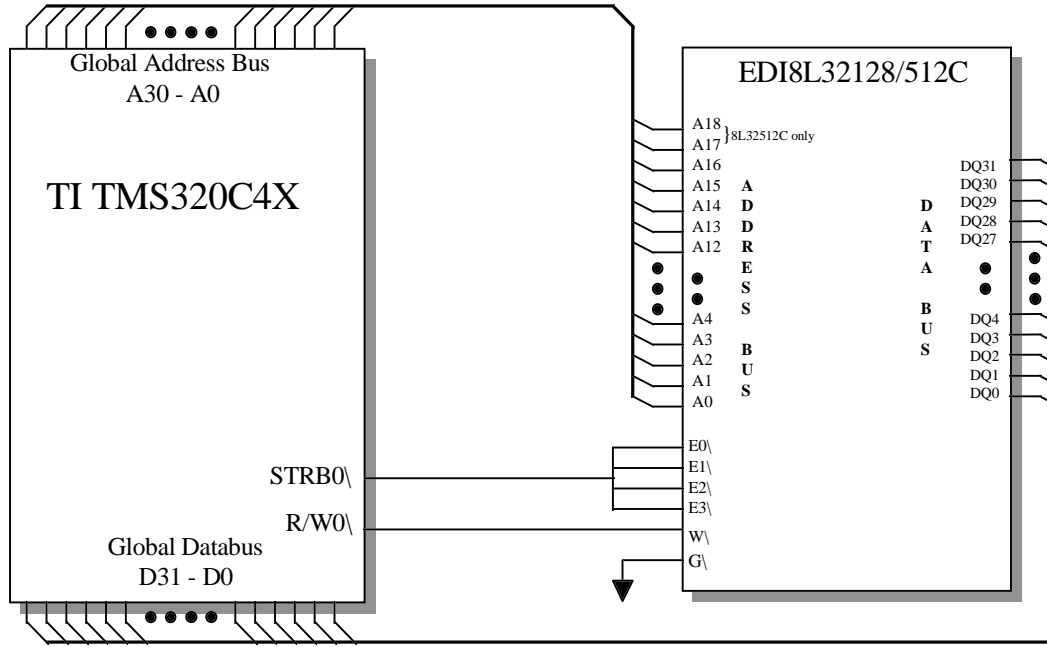
Figure 3. Basic Interface of TMS320C4x to the EDI8L3265C or EDI8L32256C



Of particular interest is the connection of the external strobe of the C30/C31 to the Enable pins of the EDI8L3265C or the 8L32256C. The byte select pins, BS0\ -BS3\, are connected directly to the strobe pin of the C4X, STRB0\ . The Chip Enable pins, E0\ - E1\, may be connected in one of two ways. E0\ and E1\ may be tied to ground or also connected to the STRB0\ pin. If E0\ and E1\ are tied to ground the device will not be able to enter low power standby mode. If connected to STRB0\ the memory will enter low power standby mode when STRB0\ pin is active high. Decision on best implementation should be based on system power requirements. Databus pins D31 - D0 of the TMS320C4x are connected to the corresponding DQ31 - DQ0 of the 8L3265C or 8L32256C.

Figure 4 shows interfacing to the EDI8L32128C or EDI8L32512C.

Figure 4. Basic Interface of TMS320C4x to the EDI8L32128C or EDI8L32512C



In this case the strobe pin of the C4X is connected to the four chip enable pins, E0\ - E3\, of the memory array. The device enters low power standby mode whenever STRB0\ of the C4X is active high. E0\ - E3\ of the 128Kx32 and 512Kx32 are located on the same device pins as the BS0\ - BS3\ pins on the 64Kx32 and 256Kx32. Therefore when considering upgrade paths the decisions required are the connection of E0\ and E1\ on the 64Kx32 and the 256Kx32 and supplying the extra address signals required for the additional density.

Databus pins D31 - D0 of the TMS320C4x are connected to the corresponding DQ31 - DQ0 of the 8L32128C/512C.

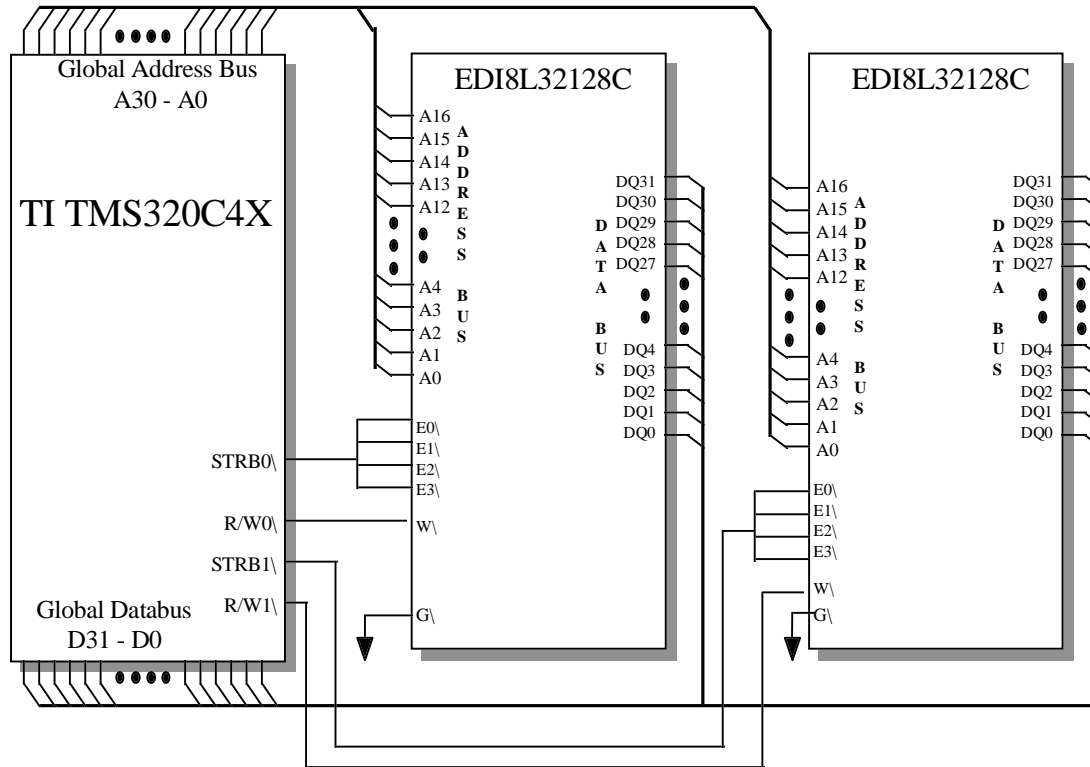


## Dual Strobe Interface (Two Memory Banks)

The TMS320C4x DSPs provide two sets of control signals for each of the external memory buses, Local and Global. This allows for interfacing to two memory banks within the memory interface without the addition of decode logic. This feature combined with the EDI's x32 SRAM products allow density options from 64Kx32 (EDI8L3265C) to 1Mx32 (2x512Kx32, two EDI8L32512C) per external memory bus.

Figure 5 shows an example of the dual strobe interface to the EDI8L32128C SRAM product. The first 128Kx32 device is connected to the STRB0\ and R/W0\ control pins while the second 128Kx32 is connected to the STRB1\ and R/W1\ control pins. The two 128Kx32 devices share the same address bus and data bus. STRB0\ and STRB1\ enable the desired 128Kx32 device when active low. Avoiding bus contention is achieved by only allowing one strobe pin low at any time. This is ensured by properly defining which part of the buses memory space is allocated to each strobe, via the memory interface control register (LMICR or MICR).

Figure 5. Dual Strobe Interface Between TMS320C4x and Two EDI8L32128C



The dual-strobe interface to other members of EDI's x32 SRAM family can be achieved in similar fashion. Simply use the basic interface shown in the previous section and use STRB1\ and R/W1\ for the second device. The dual-strobe interface is applicable to both the Global and Local Bus interfaces.



## Matching Memory Access to DSP Bus Frequency

Table 6 compares the various DSP speed options available in the TMS320C4x family and the EDI x32 MCM-L SRAM device part number required for Zero wait state operation.

*Table 6. Memory Access Time versus DSP Bus Frequency*

DSP	External Bus Cycle Time	Memory Access Required (2)	EDI Part Number (1)	Memory Access
TMS320C32-60	33nS	16nS	EDI8L32XXXC15AC	15nS
TMS320C3X-50	40nS	21nS	EDI8L32XXXC20AC	20nS

- Notes: 1) XXX in EDI part number refers to device density as follows:  
 65=64Kx32  
 128=128Kx32  
 256=256Kx32  
 512=512Kx32
- 2) Requirements may differ depending on system board design, capacitive loading, signal line lengths etc. For example the 16nS memory requirement for the TMS320C4x-60 could be met with the 15nS EDI device. However under non-ideal conditions (heavy loading etc.) the 1nS guardband may not be sufficient and may require the next fastest access memory component. In this example the EDI8L32XXXB12, with a 12 nS, access may be required.



## Summary

EDI's x32 MCM-L SRAM product family provides an ideal memory solution for the TMS320C4x family of DSPs. In addition to the space savings typically associated with module approaches, EDI's x32 SRAM family also provides a wide variety of density and speed performance options within the same 68 pin PLCC package. Densities are available from 64Kx32 through 512Kx32 and access speeds from 8nS through 25nS. This wide range of options allows system designers to provide a system design with multiple options and the ability to use single designs across multiple applications.

The single address bus, data bus and write enable pin provides an easy interface to the TMS320C4x family of DSPs that requires no additional logic.





## References

TMS320C4x User's Guide

EDI8L3265C Datasheet

EDI8L32128C Datasheet

EDI8L32256C Datasheet

EDI8L32512C Datasheet